

SPTECH Silicon NPN Power Transistor

2SC2555

DESCRIPTION

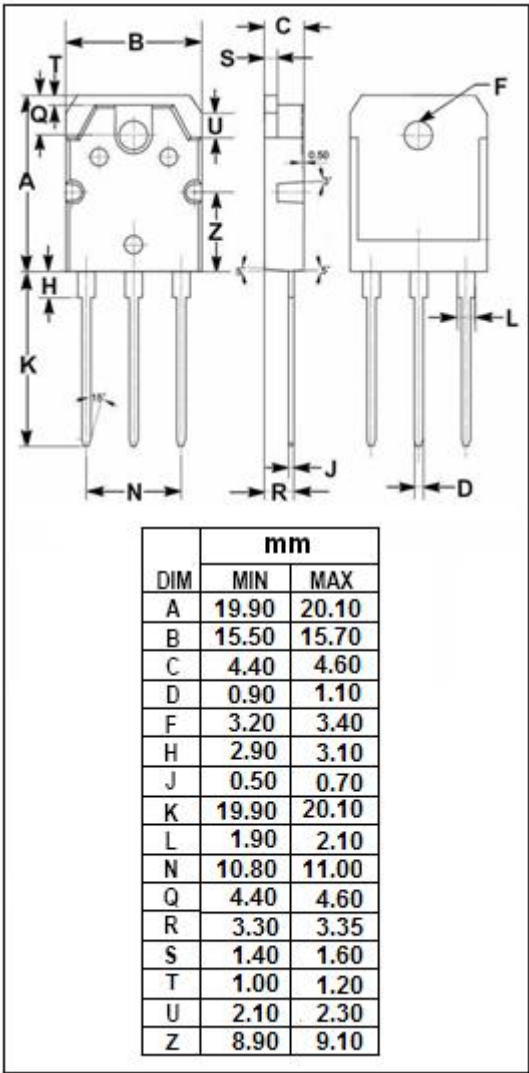
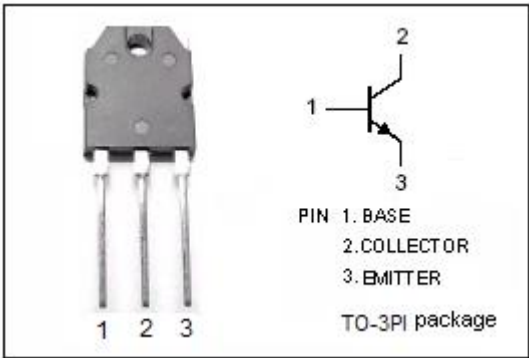
- High Collector-Emitter Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed

APPLICATIONS

- Switching regulator and high voltage switching applications
- High speed DC-DC converter applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	4	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	80	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



SPTECH Silicon NPN Power Transistor**2SC2555****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$; $I_B = 0$	400			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 1\text{mA}$; $I_E = 0$	500			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 4\text{A}$; $I_B = 0.8\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 4\text{A}$; $I_B = 0.8\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 400\text{V}$; $I_E = 0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 7\text{V}$; $I_C = 0$			1	mA
h_{FE-1}	DC Current Gain	$I_C = 1\text{A}$; $V_{CE} = 5\text{V}$	15			
h_{FE-2}	DC Current Gain	$I_C = 4\text{A}$; $V_{CE} = 5\text{V}$	10			